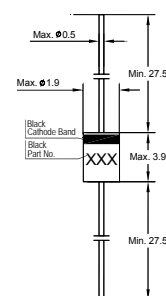


Silicon Epitaxial Planar Diodes



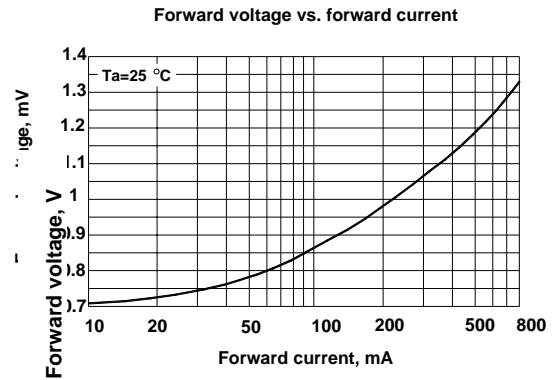
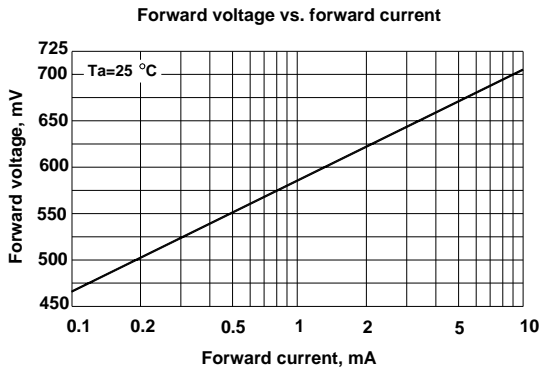
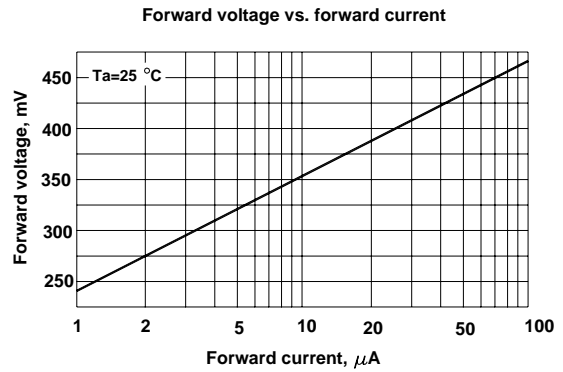
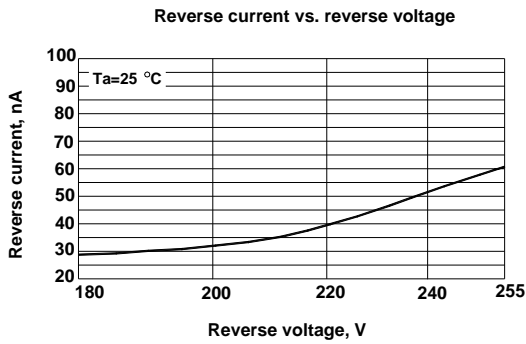
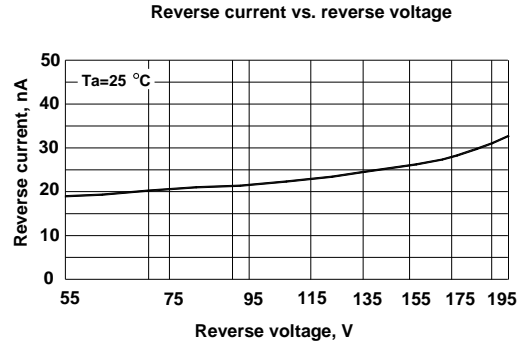
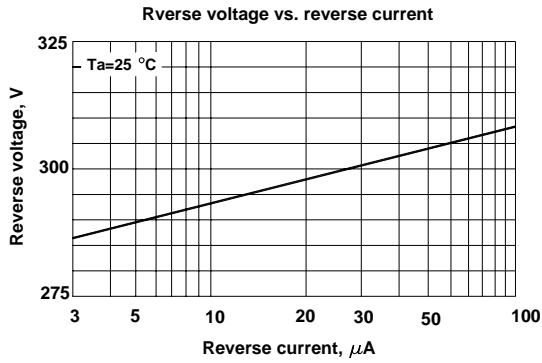
Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

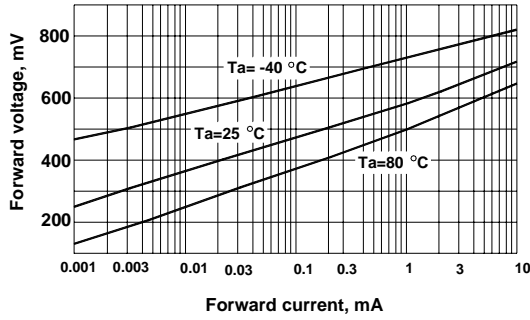
Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	120	V
		200	
		250	
Reverse Voltage	V_R	100	V
		150	
		200	
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$ 1	A
		at $t = 100\text{ }\mu\text{s}$ 3	
		at $t = 1\text{ }\mu\text{s}$ 9	
Total Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

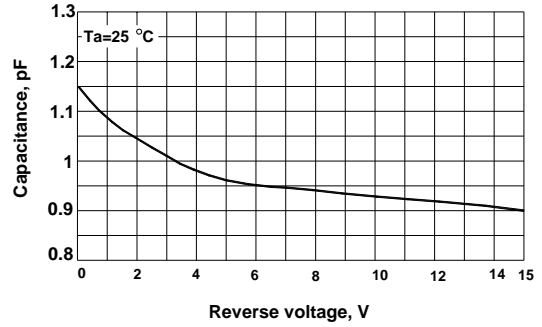
Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	120	-	V
		200	-	
		250	-	
Reverse Current	I_R	-	100	nA
at $V_R = 100\text{ V}$			100	nA
at $V_R = 150\text{ V}$			100	nA
at $V_R = 200\text{ V}$		-	100	μA
at $V_R = 100\text{ V}, T_A = 150\text{ }^\circ\text{C}$		-	100	μA
at $V_R = 150\text{ V}, T_A = 150\text{ }^\circ\text{C}$		-	100	μA
at $V_R = 200\text{ V}, T_A = 150\text{ }^\circ\text{C}$	-	100	μA	
Forward Voltage	V_F	-	1	V
at $I_F = 100\text{ mA}$			1.25	
Diode Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_d	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30\text{ mA}, I_{rr} = 3\text{ mA}, R_L = 100\text{ }\Omega$	t_{rr}	-	50	ns



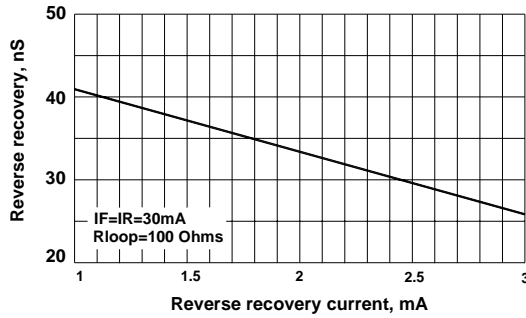
Forward voltage vs. ambient temperature



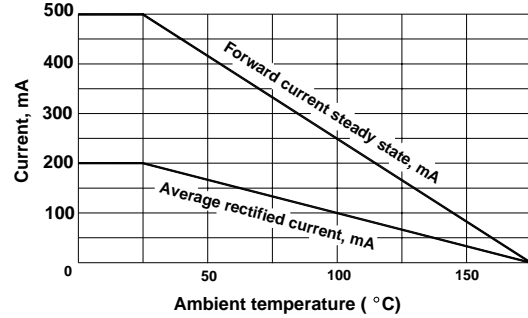
Capacitance vs. reverse voltage



Reverse recovery time vs. reverse recovery current



Average rectified current & forward current vs. ambient temperature



Power derating curve

